

#### **Features**

• 30V/70A

 $R_{DS (ON)} = 3m\Omega(Typ.)@V_{GS} = 10V$ 

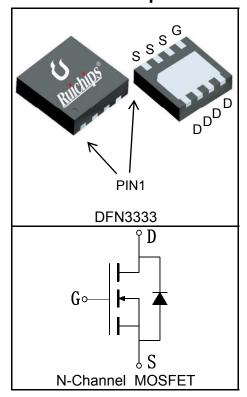
 $R_{DS (ON)} = 3.6 \text{m}\Omega(\text{Typ.})@V_{GS} = 4.5 \text{V}$ 

- Uses Ruichips advanced TrenchTM technology
- Excellent QgxR<sub>DS(on)</sub> product(FOM)
- 100% avalanche tested
- · Qualified according to JEDEC criteria
- Lead Free and Green Device Available (RoHS Compliant)

### **Applications**

- Switching Application Systems
- On Board power for server
- DC/DC Converters

### **Pin Description**



## **Absolute Maximum Ratings**

Symbol	Parameter	Rating	Unit				
Common Ratings (T <sub>c</sub> =25°C Unless Otherwise Noted)							
V <sub>DSS</sub>	Drain-Source Voltage	30	V				
$V_{GSS}$	Gate-Source Voltage		±20	V			
T <sub>J</sub>	Maximum Junction Temperature		150	°C			
T <sub>STG</sub>	Storage Temperature Range			°C			
I <sub>S</sub>	Diode Continuous Forward Current	20	Α				
Mounted on Large Heat Sink							
I <sub>DP</sub> (1)	300µs Pulse Drain Current Tested	T <sub>C</sub> =25°C	250	Α			
I <sub>D</sub> <sup>②</sup>	Continuous Drain Current@ $T_C(V_{GS}=10V)$ $ T_C=25^{\circ}C $ $ T_C=100^{\circ}C $		70				
			45				
	0 D . 0	T <sub>A</sub> =25°C	20	A			
	Continuous Drain Current@T <sub>A</sub> (V <sub>GS</sub> =10V) <sup>(3)</sup>	T <sub>A</sub> =70°C	16				
$P_{D}$	Maximum Power Dissipation@T <sub>C</sub>	T <sub>C</sub> =25°C	45				
	T <sub>C</sub> =100°C		18	W			
		T <sub>A</sub> =25°C	3.6	VV			
	Maximum Power Dissipation@ $T_A^{(3)}$ $T_A = 70^{\circ}C$		2.3				

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Symbol	Parameter	Rating	Unit			
$R_{ heta JC}$	Thermal Resistance-Junction to Case	2.8	°C/W			
$R_{ hetaJA}^{\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ $	Thermal Resistance-Junction to Ambient	35	°C/W			
Drain-Source Avalanche Ratings						
E <sub>AS</sub>	Avalanche Energy, Single Pulsed	156	mJ			

# $\textbf{Electrical Characteristics} \; (T_{\text{C}}\text{=}25^{\circ}\text{C Unless Otherwise Noted})$

Cumbal	Darameter	Toot Condition	RU3070M3			Unit		
Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Unit		
Static Characteristics								
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>DS</sub> =250μA	30			V		
1	Zero Gate Voltage Drain Current	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V			1	πΔ		
I <sub>DSS</sub>		T <sub>J</sub> =125°C			30	μA		
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$ , $I_{DS}=250\mu A$	1		2.5	V		
I <sub>GSS</sub>	Gate Leakage Current	$V_{GS}$ =±20V, $V_{DS}$ =0V			±100	nA		
<b>5</b>	D : 0	V <sub>GS</sub> =10V, I <sub>DS</sub> =20A		3	3.6	mΩ		
R <sub>DS(ON)</sub> <sup>(5)</sup>	Drain-Source On-state Resistance	V <sub>GS</sub> =4.5V, I <sub>DS</sub> =16A		3.6	4.2	mΩ		
Diode Cha	Diode Characteristics							
V <sub>SD</sub>	Diode Forward Voltage	I <sub>SD</sub> =20A, V <sub>GS</sub> =0V			1.2	V		
trr	Reverse Recovery Time	L		30		ns		
Qrr	Reverse Recovery Charge	IsD=20A, dIsD/dt=100A/µs		34		nC		
Dynamic C	Characteristics <sup>©</sup>							
$R_{G}$	Gate Resistance	V <sub>GS</sub> =0V,V <sub>DS</sub> =0V,F=1MHz		1.8		Ω		
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V,		3270				
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> =15V, Frequency=1.0MHz		580		pF		
C <sub>rss</sub>	Reverse Transfer Capacitance	Trequency 1.0WHZ		285				
t <sub>d(ON)</sub>	Turn-on Delay Time			8				
t <sub>r</sub>	Turn-on Rise Time	V <sub>DD</sub> =15V, I <sub>DS</sub> =20A,		12		ns		
t <sub>d(OFF)</sub>	Turn-off Delay Time	$V_{GEN}$ =10V, $R_{G}$ =3 $\Omega$		35				
t <sub>f</sub>	Turn-off Fall Time			9				
Gate Char	ge Characteristics <sup>®</sup>							
Q <sub>g</sub>	Total Gate Charge			60				
Q <sub>gs</sub>	Gate-Source Charge	V <sub>DS</sub> =24V, V <sub>GS</sub> =10V, I <sub>DS</sub> =20A		15		nC		
$Q_{gd}$	Gate-Drain Charge	ייט בטיי		22				



Notes:

①Pulse width limited by safe operating area.

2Calculated continuous current based on maximum allowable junction temperature.

The package limitation current is 40A.

③When mounted on 1 inch square copper board, t≤10sec.

4Limited by TJmax, IAS =25A, VDD = 24V, RG =  $50\,\Omega$ , Starting TJ =  $25^{\circ}$  C.

⑤Pulse test;Pulse width≤300μs, duty cycle≤2%.

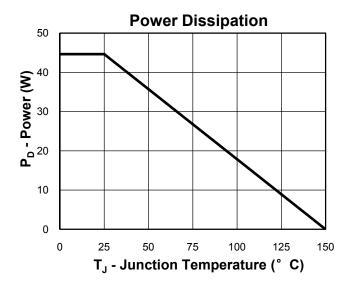
@Guaranteed by design, not subject to production testing.

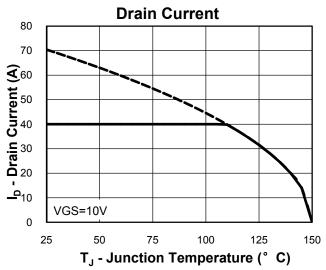
## **Ordering and Marking Information**

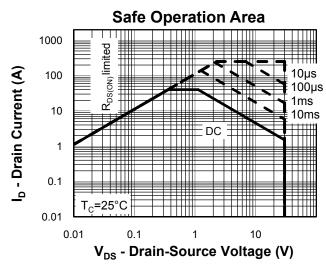
Device	Marking	Package	Packaging	Quantity	Reel Size	Tape width
RU3070M3	RU3070	DFN3333	Tape&Reel	5000	13"	12mm

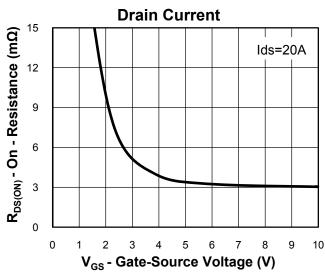


# **Typical Characteristics**

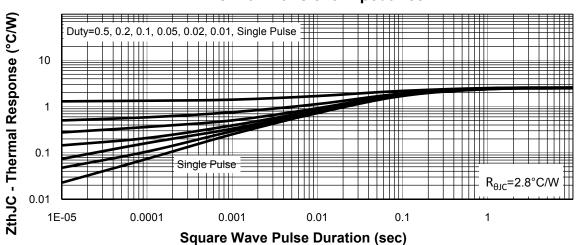






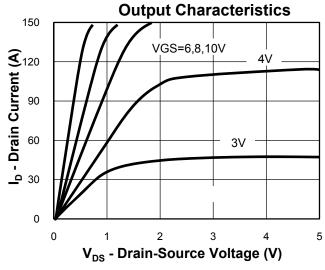


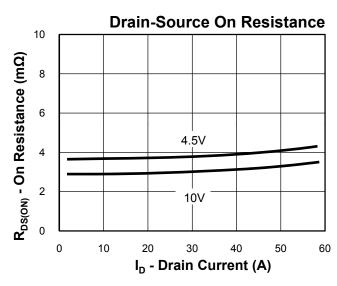
#### **Thermal Transient Impedance**

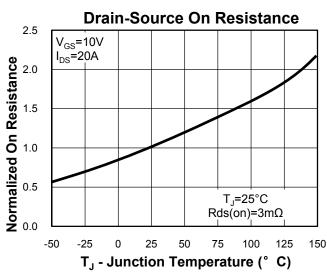


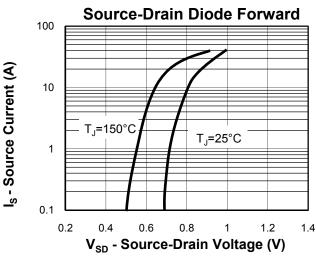


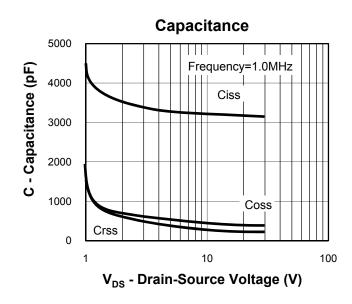
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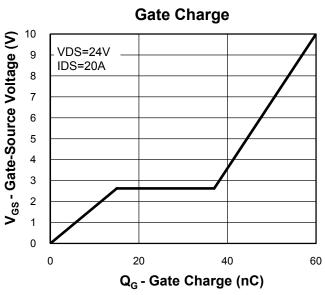








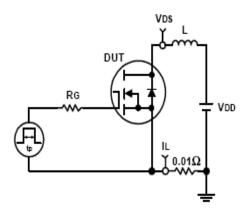


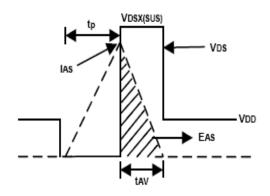


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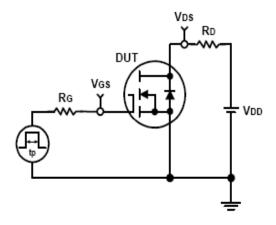
## **Avalanche Test Circuit and Waveforms**

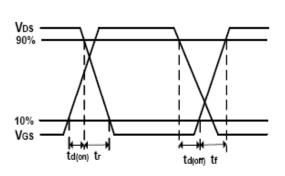




# **Switching Time Test Circuit and Waveforms**

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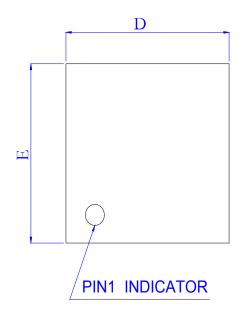


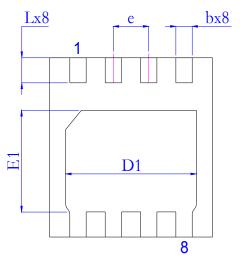


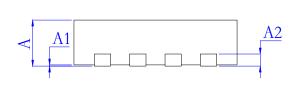


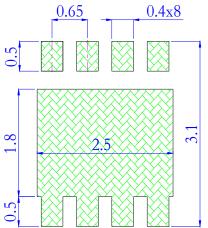
# **Package Information**

# **DFN3333**









Land Pattern (Only for Reference)

SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.700	0.750	0.800	0.028	0.030	0.031
A1	0.000	0.020	0.050	0.000	0.001	0.002
A2	0.203 REF.			0.008 REF.		
b	0.250	0.300	0.350	0.010	0.012	0.014
D	3.000	3. 150	3.300	0.118	0. 124	0.130
D1	2.350	2.400	2.450	0.093	0.094	0.096
Е	3.000	3. 150	3.300	0.118	0. 124	0.130
E1	1.650	1.700	1.750	0.065	0.067	0.069
е	0. 650BSC			0. 026BSC		
L	0.370	0.420	0.470	0.015	0.017	0.019

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